

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|--|---|------------------|---------|------------------|
| L1 | 9591 | (@ad<"20010612") and gate and (semiconductor or "ic" or chip or die) and (locos or ((dielectric or insulation) near (trench or gap or recess or via))) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/02 13:43 |
| L2 | 5214 | (@ad<"20010612") and 438/196, 207,218,219,248,294,295,296, 318,353,355,359,391,404,439, 362,297,225.ccls. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/02 13:44 |
| L3 | 3017 | L2 and gate | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/02 14:03 |
| L4 | 785 | L2 and memory | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/02 14:04 |
| L5 | 591 | L4 and ((etch or etching) with (oxide or insulation or dielectric)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/02 14:06 |
| L6 | 32 | L4 and (((etch or etching) and cleaning) with (oxide or insulation or dielectric)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/02 14:48 |
| L7 | 22 | L4 and (((first and second) near (etch or etching)) with (oxide or insulation or dielectric)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/02 14:49 |